

# Press Release

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## **IHP Leibniz-institute in Frankfurt (Oder) organizes international semiconductor conference for scientists, engineers and experts GADEST 2019 conference will take place for the 18<sup>th</sup> time**

**Frankfurt (Oder).** From 22<sup>nd</sup> to 27<sup>th</sup> of September the 18<sup>th</sup> Conference on Gettering and Defect Engineering in Semiconductor Technology (GADEST) organized by IHP – Innovations for High Performance Microelectronics will take place in Zeuthen/Germany. The GADEST conference series provides a forum for interaction between scientists and engineers engaged in the field of semiconductor defect physics, materials science and device technology. “The conference is focused on fundamental aspects as well as technological problems associated with defects in electronic materials and devices ranging from microelectronics to photovoltaics.” explains Dr. Gudrun Kissinger, conference chairwoman and scientist at IHP. About 120 participants from 24 countries worldwide are registered for GADEST 2019.

The topics can be summarized into three main categories: The first category includes the optimization of silicon (Si) as host material for improved electronic and photovoltaic device function. It spans from crystal growth, defect and impurity engineering, stress engineering, source-drain and channel engineering, optimization of doping profiles, to interface and gate engineering. The second category involves the design of heterosystems including material components other than Si as host material for improved and new device functionalities. Main fields are high frequency Si/Ge-electronics on Si, high mobility channel materials, heterogeneously integrated (III – V / Si) photonics, heavily doped carbon nanotubes as contacts. The third category includes basic research on device physics, point defects, getter effects, and extended defects. In the center of interest are results obtained by spectroscopic methods, advanced measurement and detection methods, ab initio calculations and predictive modeling.

Starting from 1985 in the former German Democratic Republic, the GADEST conference is biennially organized. Until 1995 it was held in Germany. Thereafter, it was hosted in various European countries. This year’s GADEST is supported by the Deutsche Forschungsgemeinschaft (DFG) and several international companies and organizations.

Local partner for this years conference is the Investor Center Ostbrandenburg GmbH (ICOB), the business development agency of Frankfurt (Oder). “Our joint aim is to use the conference to introduce the international audience to opportunities rising from potential investment or cooperation projects in the region,” explains Christopher Nüßlein, managing director of ICOB the preparation for the upcoming conference.



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View into the Molecular Beam Epitaxy (MBE) Lab of IHP. MBE is a process of physical vapor deposition to produce crystalline thin films (or layer systems). It is used in nanotechnology, for example. © IHP/Mausolf 2019

## Further Information:

Conference Website: <https://www.gadest2019.org/index.php>

ICOB: <http://www.icob.de>

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## About IHP:

IHP is an institute of the Leibniz Association and conducts research and development of silicon-based systems and ultrahigh frequency circuits and technologies including new materials. It develops innovative solutions for application areas such as wireless and broadband communication, security, medical technology, industry 4.0, automotive industry, and aerospace. IHP employs approximately 300 people. It operates a pilot line for technological developments and the preparation of high-speed circuits with 0.13/0.25  $\mu\text{m}$  BiCMOS technologies, located in a 1000 m<sup>2</sup> class 1 cleanroom.

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